

isc Silicon NPN Power Transistor

isc website: www.iscsemi.com

2SD1313

DESCRIPTION 2 High Power Dissipation · High Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= 350V(Min) · High Speed Switching · Low Collector Saturation Voltage PIN 1. BASE 2.COLLECTOR · Minimum Lot-to-Lot variations for robust device 3. BMITTER performance and reliable operation TO-3PL package 2 2 **APPLICATIONS** в • High power amplifier applications. · High power switching applications. ABSOLUTE MAXIMUM RATINGS(T_a=25℃) Ŕ SYMBOL PARAMETER VALUE UNIT 0 800 Collector-Base Voltage V V_{CBO} F2PL VCEO Collector-Emitter Voltage 350 V Emitter-Base Voltage 7 V_{EBO} V -000 **Collector Current-Continuous** 25 lc А mm DIM MIN MAX 26.50 Collector Current-Pulse А 25.50 35 А Ісм 19.80 20.20 В 5.50 4.50 C 1.10 **Base Current-Continuous** 10 D 0.90 I_B А Ε 3.20 2.80 F 2.40 2.60 Base Current- Pulse us 15 А **I**BM 10.80 11.00 G Н 3.10 3.30 0.70 0.50 J **Collector Power Dissipation** Pc 200 W Κ 21.00 20.00 @ Tc=25°C Ν 3.90 4.50 P 2.40 2.60 $T_{\rm J}$ Junction Temperature 150 °C Q 3.10 3.50 2.60 R 1.90 3.90 4.10 U -55~150 °C Storage Temperature Range Tstg W 2.90 3.25

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ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _c = 10mA; I _B = 0	350			V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 15A; I _B = 3A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 15Α; I _B = 3Α			1.7	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C = 0			1	mA
h _{FE-1}	DC Current Gain	Ic= 1A; Vce= 5V	15			
h _{FE-2}	DC Current Gain	I _C = 25A; V _{CE} = 5V	6			
Сов	Output Capacitance	I _E =0; V _{CB} = 50V; f _{test} = 1MHz		170		pF
f _T	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 10V		6		MHz

Switching Times

t _{on}	Turn-on Time	Ic= 15A; I _{B1} = I _{B2} = 3A; R _L = 13.3 Ω; V _{CC} ≈ 200V P _W =20 μ s; Duty Cycle≤1%	0.8	μ S
tstg	Storage Time		3.0	μs
tr	Fall Time		0.5	μS

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